



## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
	3.2mΩ @ V <sub>GS</sub> = 10V	100A
30V	5.5mΩ @ V <sub>GS</sub> = 4.5V	85A

## Description

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$ , yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Backlighting
- Power Management Functions
- DC-DC Converters

### **30V N-CHANNEL ENHANCEMENT MODE MOSFET**

## **Features and Benefits**

- Low R<sub>DS(ON)</sub> Ensures On-State Losses are Minimized
- Excellent Q<sub>GD</sub> × R<sub>DS(ON)</sub> Product (FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## Mechanical Data

- Case: PowerDl<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (£3)

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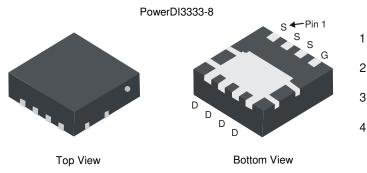
• Weight: 0.008 grams (Approximate)

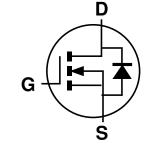
Top View

Internal Schematic

SG2 = Product Type Marking Code

YYWW = Date Code Marking YY = Last Digit of Year (ex: 16 = 2016) WW = Week Code (01 to 53)





Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3003LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT3003LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied. 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



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# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	30	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	ID	100 90	А
Continuous Drain Current (Note 5) $V_{GS} = 10V$ $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		ID	22 18	А
Maximum Continuous Body Diode Forward Current (Note 5)	ls	3	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	100	А	
Avalanche Current, L=1mH	I <sub>AS</sub>	16	А	
Avalanche Energy, L=1mH	E <sub>AS</sub>	250	mJ	

## **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	PD	2.4	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	52	°C/W	
Total Power Dissipation (Note 5)	PD	62	W	
Thermal Resistance, Junction to Case (Note 6)		R <sub>eJC</sub>	2	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—		V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	—	_	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	$V_{GS} = +20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance		—	2.4	3.2	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	4	5.5	111122	$V_{GS} = 4.5V, I_D = 15A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.75	1	V	$V_{GS} = 0V, I_{S} = 10A$	
DYNAMIC CHARACTERISTICS (Note 8)						·	
Input Capacitance	CISS	_	2,370	_			
Output Capacitance	Coss	_	1,360	—	pF		
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	240	_			
Gate Resistance	R <sub>G</sub>	_	0.6	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>		20	_		V <sub>DS</sub> = 15V, I <sub>D</sub> = 20A	
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	_	44	_	nC		
Gate-Source Charge	Q <sub>GS</sub>		7	_	nc		
Gate-Drain Charge	Q <sub>GD</sub>	_	8	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.2	_		$V_{DD} = 15V, V_{GS} = 10V,$ $R_L = 0.75\Omega, R_G = 3\Omega, I_D = 20A$	
Turn-On Rise Time	t <sub>R</sub>		4.3	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>		21	_	ns		
Turn-Off Fall Time	tF		8		1		
Bodyy Diode Reverse Recovery Time	t <sub>RR</sub>	—	25		ns		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>		37	_	nC	- I <sub>F</sub> = 15A, di/dt = 500A/μs	

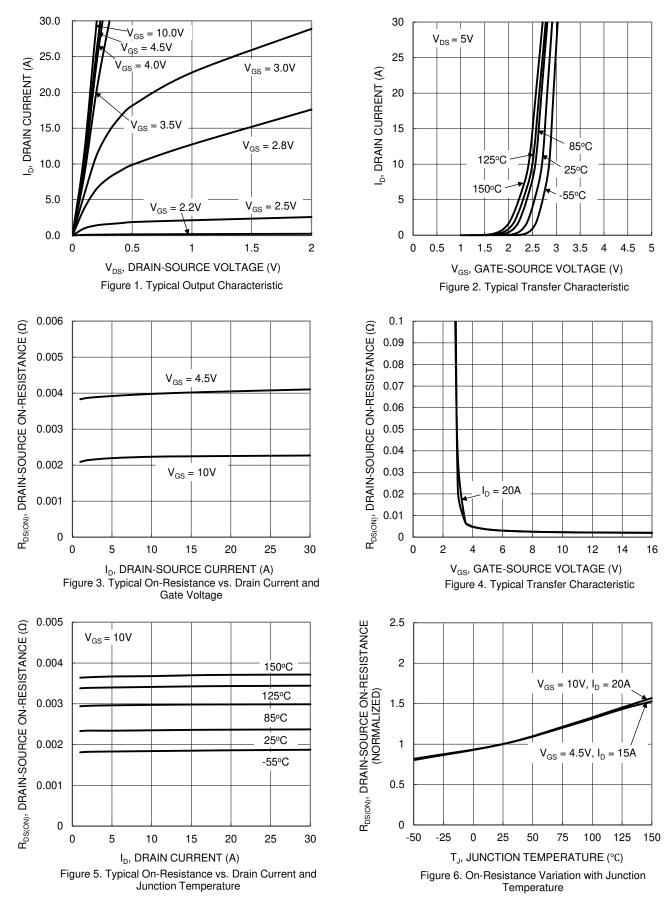
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).

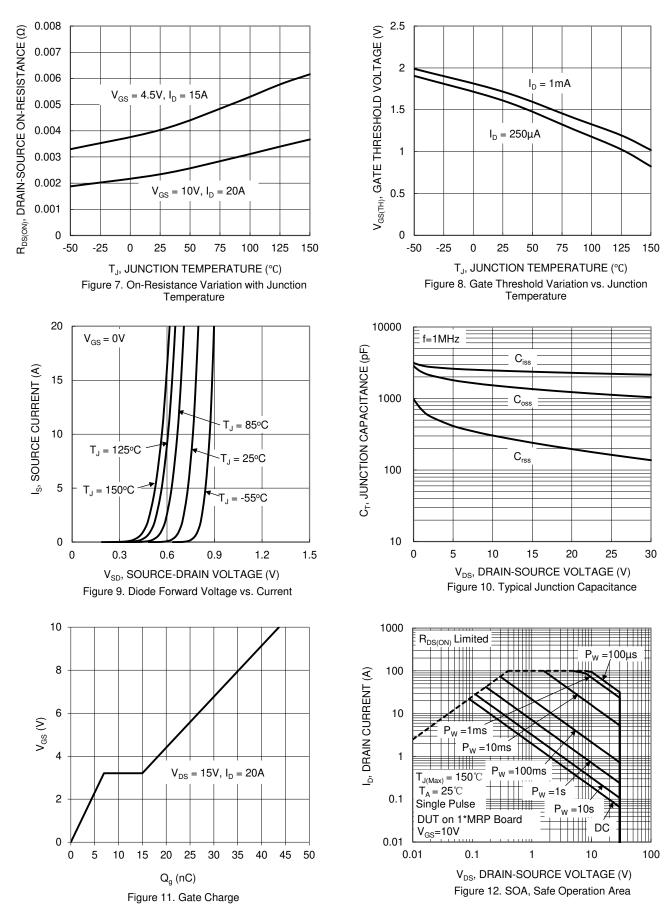
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



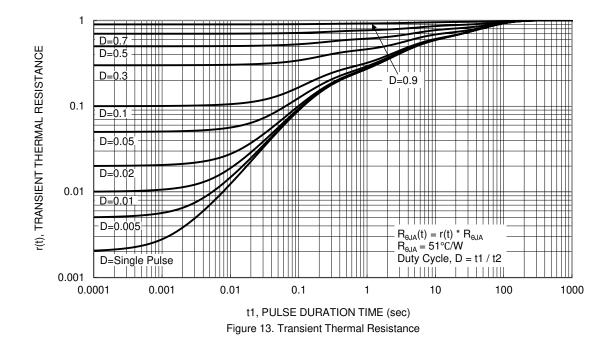






DMT3003LFG Document number: DS37819 Rev. 2 - 2

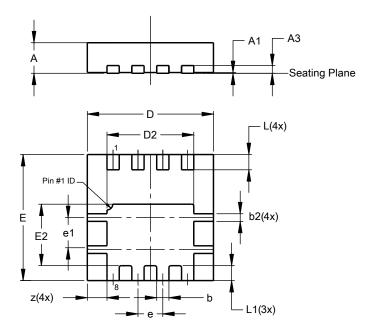






## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



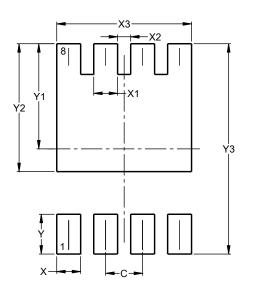
### PowerDI3333-8

PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	_	-	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
е	_	_	0.65			
e1	0.79	0.89	0.84			
L	0.35	0.45	0.40			
L1	_	-	0.39			
z	_	-	0.515			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8



Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
X3	2.370		
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		



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